

## Trench MOS Barrier Schottky Rectifier

### DO-201AD

1 1 LS 0 0 AT 2



Cathode  Anode 

### Features

- Advanced trench technology
- Low forward voltage drop
- Low power losses
- High efficiency operation
- Lead Free Finish, RoHS Compliant

### Applications

- DC/DC Converters
- AC/DC Adaptors
- Switching Power Supplies
- Freewheeling Diodes

### Maximum ratings and electrical characteristics (T<sub>J</sub> = 25°C unless otherwise noted)

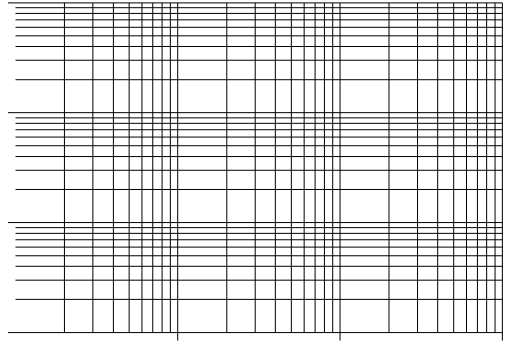
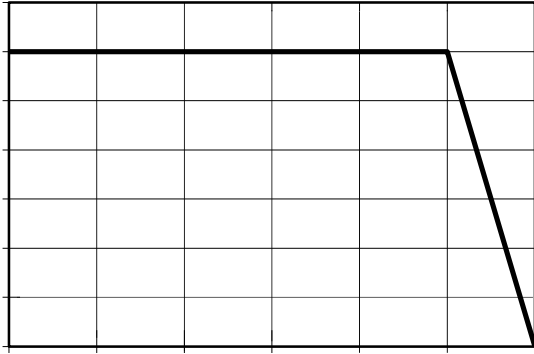
Parameter		Symbol	Limit		Unit	
Maximum repetitive peak reverse voltage		VRRM	100		V	
Maximum average forward rectified current		IF(AV)	12		A	
Peak forward surge current 8.3 ms single half sine- wave superimposed on rated load per diode		IFSM	200		A	
Operating junction and storage temperature range		TJ, TSTG	-5 to +150		°C	
Typical thermal resistance per leg		R <sub>JC</sub>	22		°C/W	
Instantaneous forward voltage per diode		VF(1)	TYP.	MAX.	V	
	IF=2A		TJ=25°C	0.41		0.44
	IF=2A		TJ=125°C	0.36		-
	IF=12A		TJ=25°C	0.62		0.67
	IF=12A		TJ=125°C	0.57		-
Instantaneous reverse current per diode at rated reverse voltage	TJ=25°C	IR(2)	20	80	uA	
	TJ=125°C		-	20	mA	

Notes:

(1) Pulse test: 300 μs pulse width, 1 % duty cycle

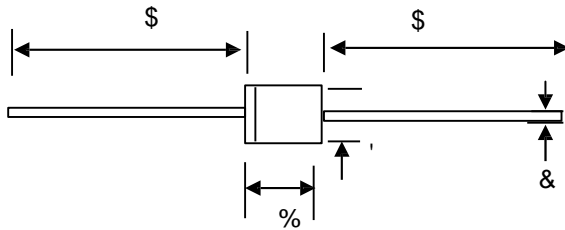
(2) Pulse test: Pulse width ≦ 40 ms

**RATINGS AND CHARACTERISTICS CURVES** (TA = 25 °C unless otherwise noted)



PACKAGE OUTLINE DIMENSIONS

DO-201AD

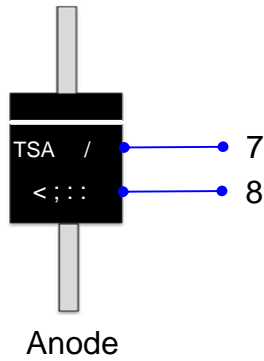


'2 \$' PHFKD QLFWD

8 1, 7		\$	%	C	'
PP	PD[			1.4	
	PLQ			1.1	
PLO	PD[			5.1	
	PLQ				

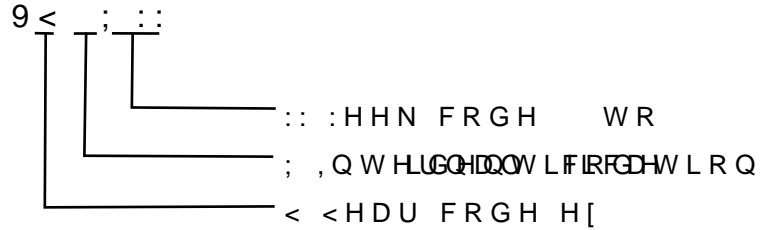
0DUNLQJ ,QIRUPDWLRQ

&DWKRGH



73URGXFW PRGH

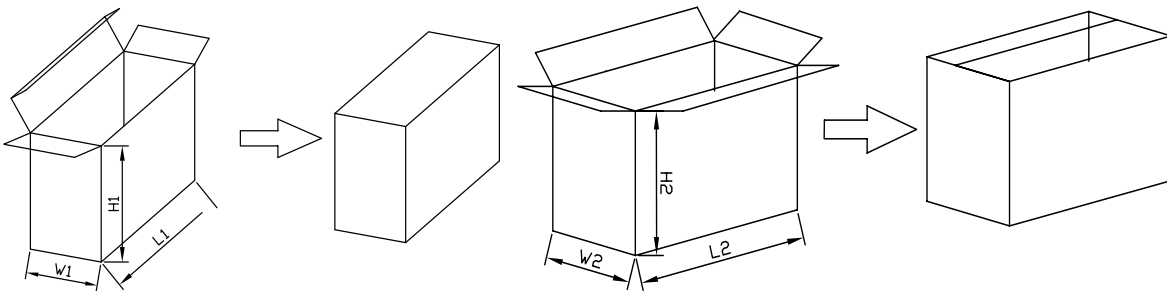
83' & LQIRUPDWLRQ



3DFNDJLQJ ,QIRUPDWLRQ

,QVLGH %R[

2XWVLGH %R[



3DFNDJLQJ ,QIRUPDWLRQ

12	81, 7	,QVLGH %R[			2XWVLGH %R[		
		/	:	+	/	:	+
6L]H	PP			4			
47<	3&6	6PDO SDVWDJH3&6 FDUWRQ			3&6 FDUWRQ HWRWDO		
1RW	7ROHUDQFH	PP" PP		PP" PP	PP" PP		